

ABSTRACT

WAFER PROCESSING METHOD

There is provided a wafer processing method including a modified layer forming step. In the wafer processing method, the power of a pulse laser beam set in the modified layer forming step is set to power that forms modified layers and cracks in such a manner that a wafer is allowed to be divided into individual device chips before the thickness of the wafer reaches a finished thickness and, after the wafer is divided into the individual device chips, the time until the thickness of the wafer reaches the finished thickness is such a time that damage due to rubbing of the individual device chips against each other is not caused through grinding under a predetermined grinding condition set in a back surface grinding step.

(Figure 2)